

Customer No.: 31561  
Application No.: 10/707,665  
Docket No.: 10755-US-PA

**REMARKS**

1. The Office Action considers the present invention into four groups and requires restriction election.

2. Applicants have preliminarily elected Group 1 with claims 1-5 for Examination.

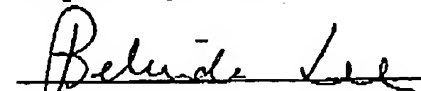
3. However, Applicant would request to consider Group 2 with claim 6-12 as the same invention.

In FIG. 4, the group 2 is to define the structure of the memory cell, which is used in Group 1 to achieve the structure of a memory device, as shown in FIG. 4. The cell structure with the transistor 402 and MOS capacitor 202, as also shown in FIG. 6, is used in the layout of the memory device.

Therefore, it is believed that the group 2 recited in claims 6-12 should be considered together with the group 1. And therefore, Applicants respectfully disagree to only elect group 1 for examination. Claims 1-12 should be considered as the same group.

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Respectfully submitted,

  
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